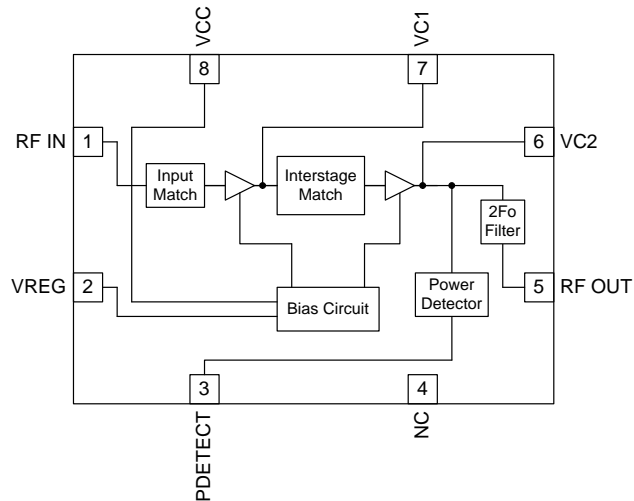


**Features**

- Single Power Supply 3.0V to 4.5V
- 30dB Typical Gain, Input Matched to 50Ω
- 2.4GHz to 2.5GHz Frequency Range
- 11g P<sub>OUT</sub> = +18dBm @ 3% Typ EVM, 95mA

**Applications**

- IEEE802.11b/g/n WLAN Applications
- 2.5GHz ISM Band Applications
- Commercial and Consumer Systems
- Portable Battery-Powered Equipment
- Spread-Spectrum and MMDS Systems



Functional Block Diagram

**Product Description**

The RF5622 is a linear, medium-power, high-efficiency, two-stage amplifier IC designed specifically for battery-powered WLAN applications such as PC cards, mini PCI, and compact flash applications. The device is manufactured on an advanced InGaP Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 2.5GHz OFDM and other spread-spectrum transmitters. The device is provided in a 2mmx2mm, 8-pin, QFN with a backside ground. The RF5622 is designed to maintain linearity over a wide range of supply voltage and power output. The RF5622 also has built-in power detector and incorporates the input and interstage matching components internally which reduces the component count used externally and makes it easier to incorporate on any design.

**Ordering Information**

|                |   |
|----------------|---|
| RF5622         | 3.0V to 4.5V, 2.4GHz to 2.5GHz Linear Power Amplifier |
| RF5622PCBA-41X | Fully Assembled Evaluation Board                      |

**Optimum Technology Matching® Applied**

- |   |                                      |                                     |                                   |
|---|--------------------------------------|-------------------------------------|-----------------------------------|
| <input type="checkbox"/> GaAs HBT             | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET          | <input type="checkbox"/> Si BiCMOS   | <input type="checkbox"/> Si CMOS    |                                   |
| <input checked="" type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT     |                                   |

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**RF5622**

*Preliminary*

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RFMD Technical Support  
at (336) 678-5570  
for more information.**